

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

OptiMOS™ Power-Transistor, 100V

OptiMOS™3 Power-Transistor
IPA086N10N3 G

Data Sheet

Rev. 2.4
Final

OptiMOS™3 Power-Transistor

Features

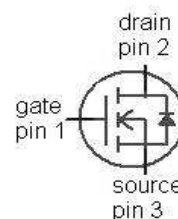
- N-channel, normal level
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC¹⁾ for target application
- Ideal for high-frequency switching and synchronous rectification
- Halogen-free according to IEC61249-2-21
- Fully isolated package (2500 VAC; 1 minute)

Product Summary

V_{DS}	100	V
$R_{DS(on),max}$	8.6	mΩ
I_D	45	A



Type	IPA086N10N3 G
	
Package	PG-TO220-FP
Marking	086N10N



Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$T_C=25\text{ °C}^{2)}$	45	A
		$T_C=100\text{ °C}$	32	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_C=25\text{ °C}$	180	
Avalanche energy, single pulse	E_{AS}	$I_D=45\text{ A}, R_{GS}=25\text{ Ω}$	170	mJ
Gate source voltage	V_{GS}		±20	V
Power dissipation	P_{tot}	$T_C=25\text{ °C}$	37.5	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 175	°C
IEC climatic category; DIN IEC 68-1			55/175/56	

¹⁾ J-STD20 and JESD22

²⁾ See figure 3

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		-	-	4	K/W
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Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$	100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=75\text{ }\mu\text{A}$	2	2.7	3.5	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=100\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$	-	0.1	1	μA
		$V_{DS}=100\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$	-	10	100	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}$, $I_D=45\text{ A}$	-	7.5	8.6	$\text{m}\Omega$
		$V_{GS}=6\text{ V}$, $I_D=23\text{ A}$	-	9.2	15.4	
Gate resistance	R_G		-	1.4	-	Ω
Transconductance	g_{fs}	$ V_{DS} >2 I_D R_{DS(on)max}$, $I_D=45\text{ A}$	35	69	-	S

³⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=50\text{ V}, f=1\text{ MHz}$	-	2990	3980	pF
Output capacitance	C_{oss}		-	523	696	
Reverse transfer capacitance	C_{rss}		-	21	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=50\text{ V}, V_{GS}=10\text{ V}, I_D=45\text{ A}, R_{G,ext}=1.6\ \Omega$	-	16	-	ns
Rise time	t_r		-	10	-	
Turn-off delay time	$t_{d(off)}$		-	27	-	
Fall time	t_f		-	8	-	

Gate Charge Characteristics⁴⁾

Gate to source charge	Q_{gs}	$V_{DD}=50\text{ V}, I_D=45\text{ A}, V_{GS}=0\text{ to }10\text{ V}$	-	14	-	nC
Gate to drain charge	Q_{gd}		-	8	-	
Switching charge	Q_{sw}		-	13	-	
Gate charge total	Q_g		-	42	55	
Gate plateau voltage	$V_{plateau}$		-	4.6	-	V
Output charge	Q_{oss}	$V_{DD}=50\text{ V}, V_{GS}=0\text{ V}$	-	55	73	nC

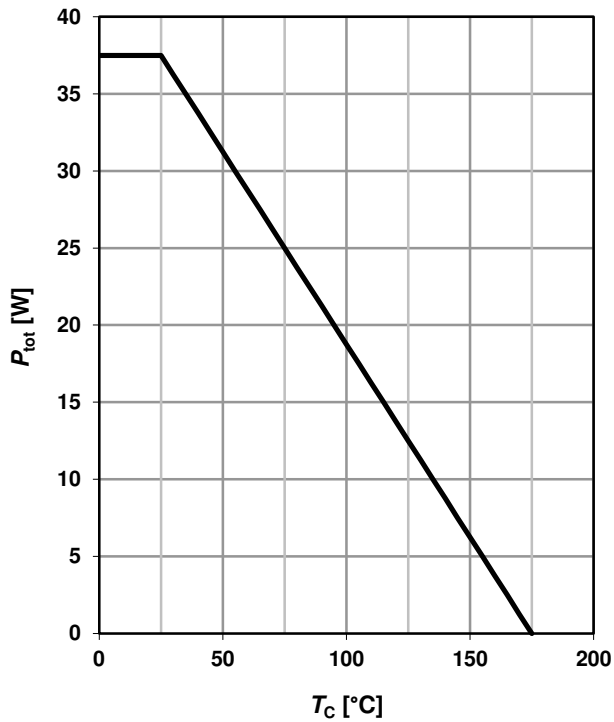
Reverse Diode

Diode continuous forward current	I_S	$T_C=25\text{ °C}$	-	-	45	A
Diode pulse current	$I_{S,pulse}$		-	-	180	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=45\text{ A}, T_j=25\text{ °C}$	-	0.9	1.2	V
Reverse recovery time	t_{rr}	$V_R=50\text{ V}, I_F=45\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$	-	63	-	ns
Reverse recovery charge	Q_{rr}		-	120	-	nC

⁴⁾ See figure 16 for gate charge parameter definition

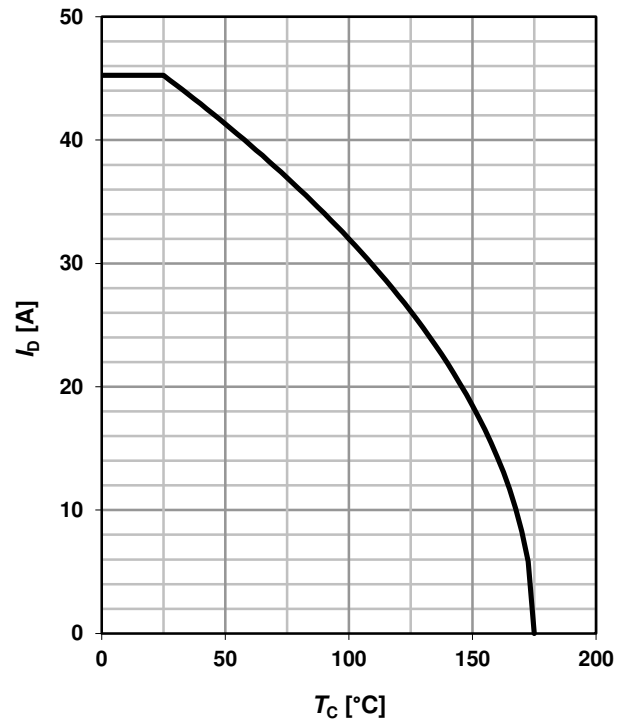
1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$



2 Drain current

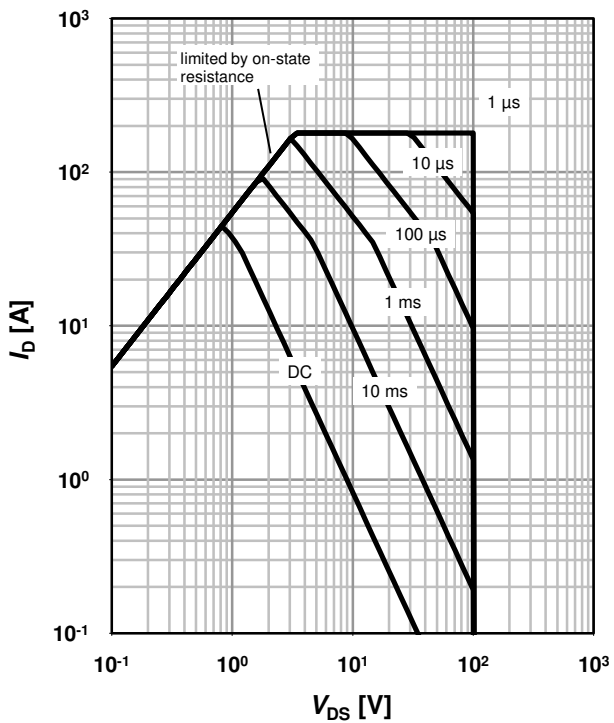
$$I_D = f(T_C); V_{GS} \geq 10 \text{ V}$$



3 Safe operating area

$$I_D = f(V_{DS}); T_C = 25 \text{ °C}; D = 0$$

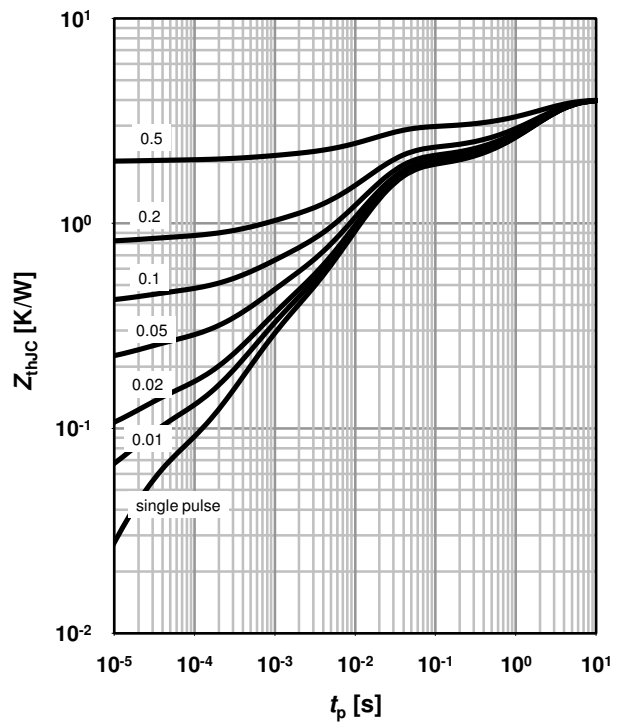
parameter: t_p



4 Max. transient thermal impedance

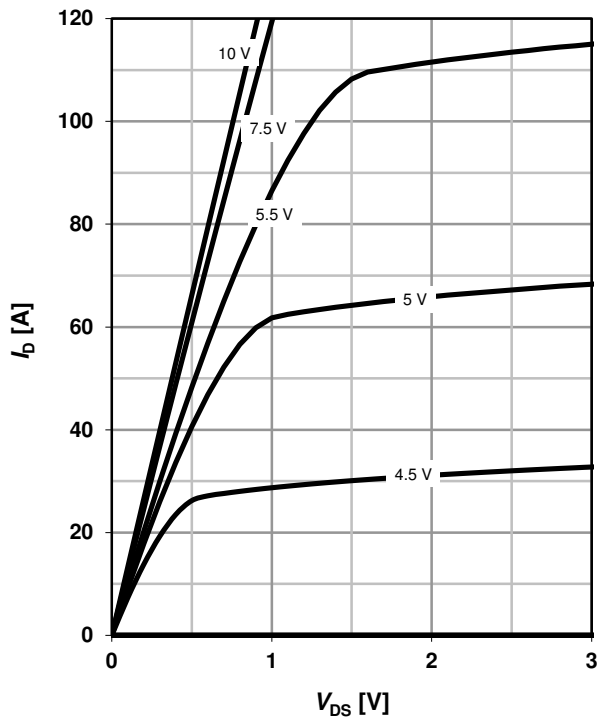
$$Z_{thJC} = f(t_p)$$

parameter: $D = t_p / T$



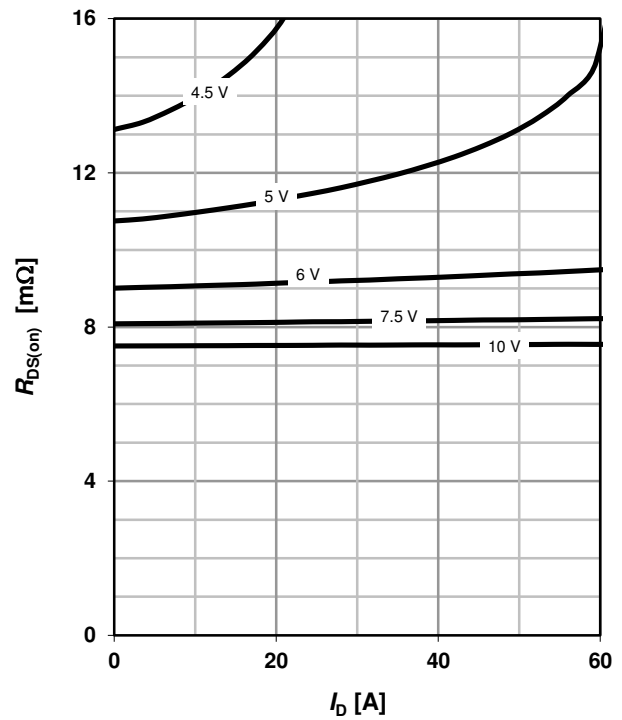
5 Typ. output characteristics

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

parameter: V_{GS}


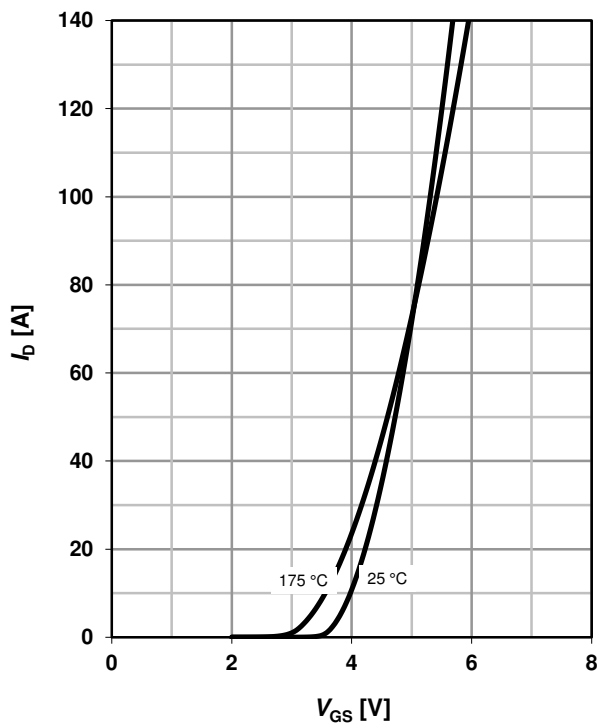
6 Typ. drain-source on resistance

 $R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$

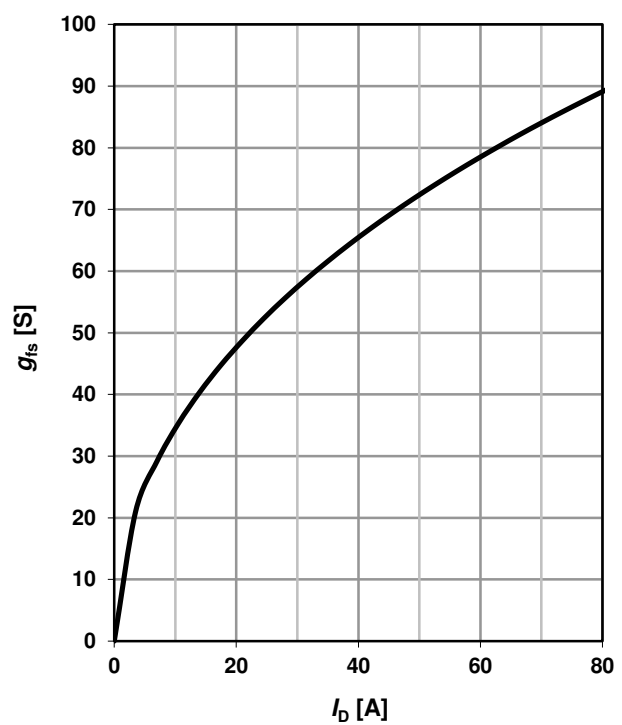
parameter: V_{GS}


7 Typ. transfer characteristics

 $I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

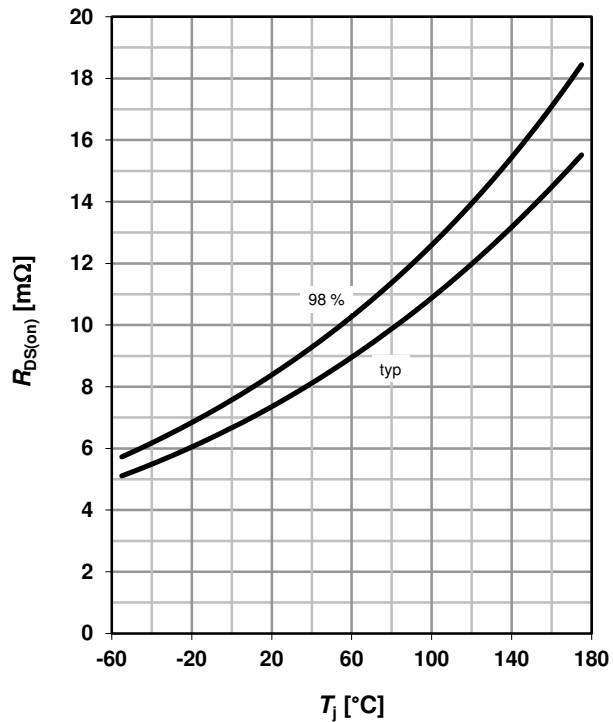
parameter: T_j


8 Typ. forward transconductance

 $g_{fs} = f(I_D); T_j = 25^\circ\text{C}$


9 Drain-source on-state resistance

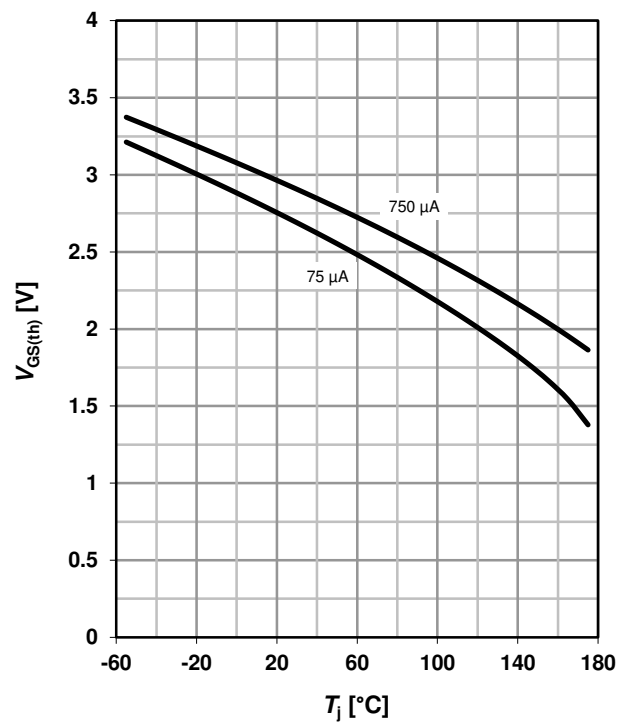
$$R_{DS(on)} = f(T_j); I_D = 45 \text{ A}; V_{GS} = 10 \text{ V}$$



10 Typ. gate threshold voltage

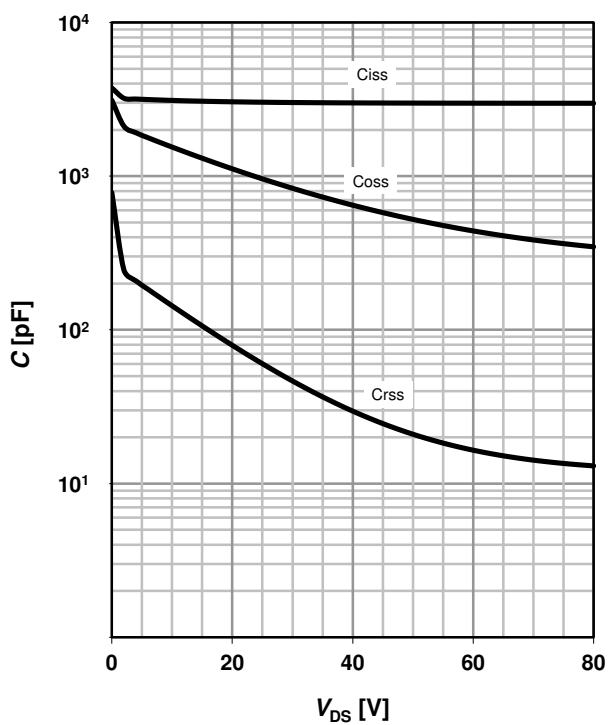
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

parameter: I_D



11 Typ. capacitances

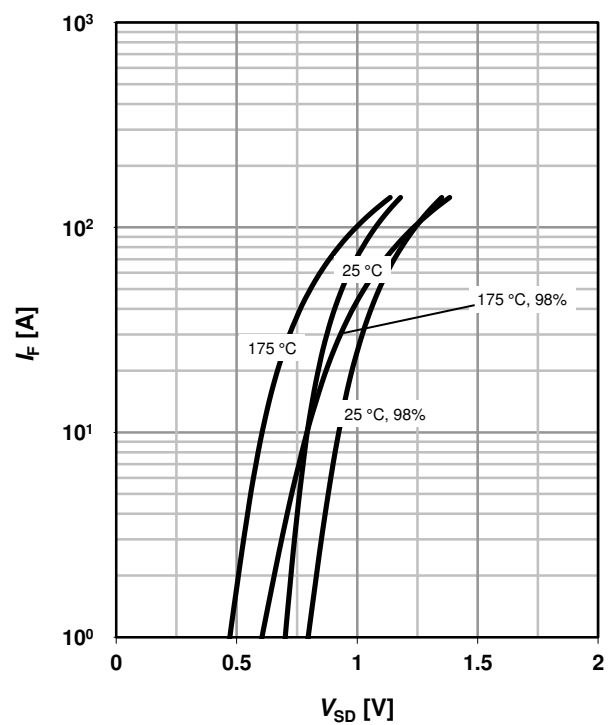
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$



12 Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

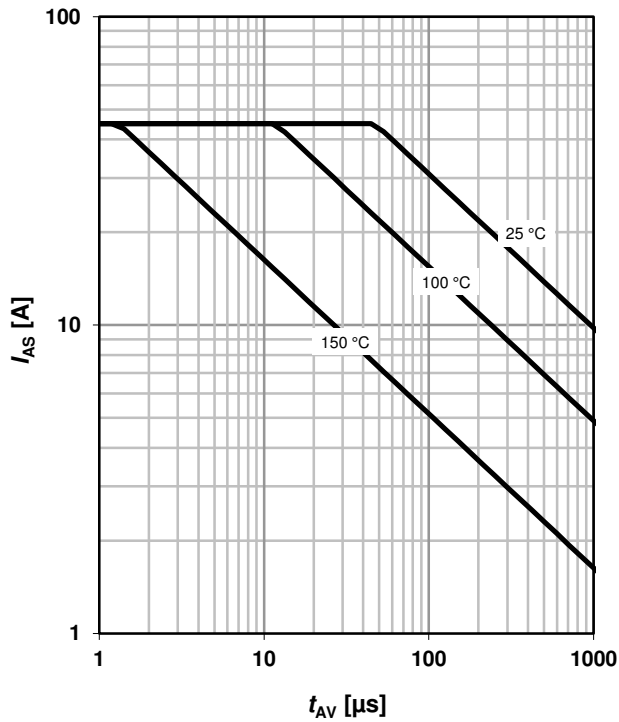
parameter: T_j



13 Avalanche characteristics

$$I_{AS}=f(t_{AV}); R_{GS}=25\ \Omega$$

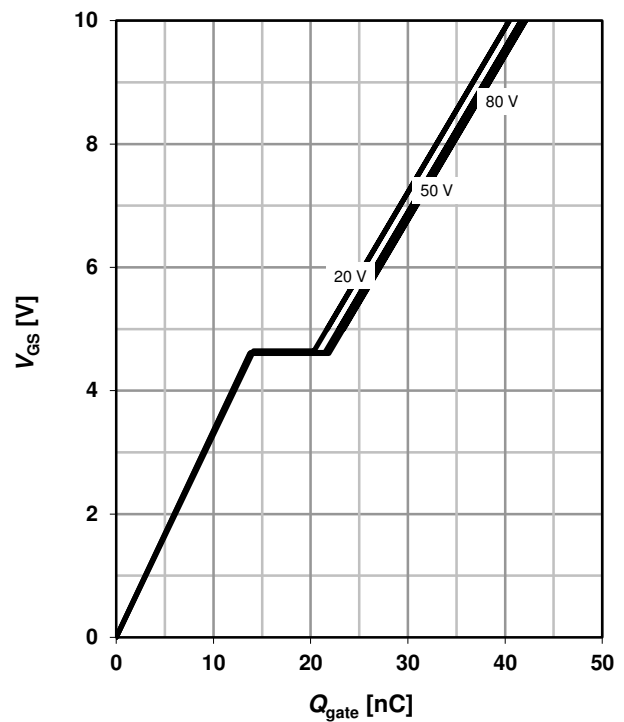
parameter: $T_{j(\text{start})}$



14 Typ. gate charge

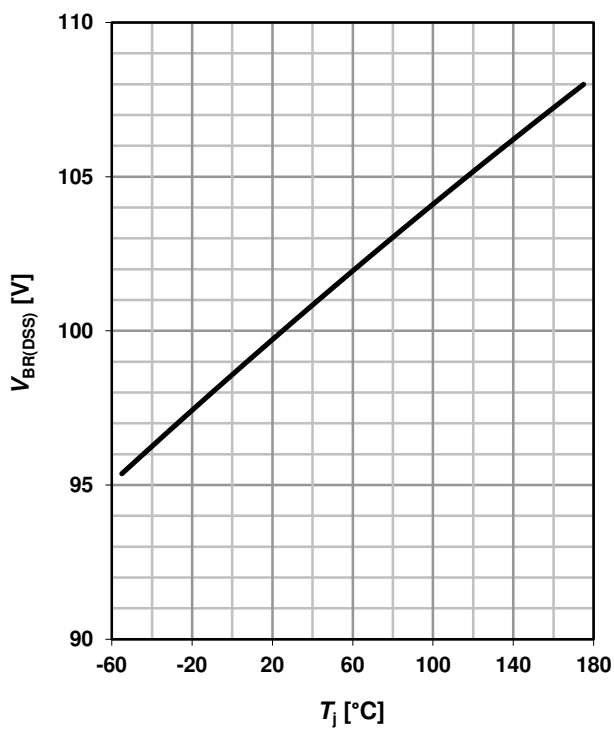
$$V_{GS}=f(Q_{\text{gate}}); I_D=45\ \text{A pulsed}$$

parameter: V_{DD}

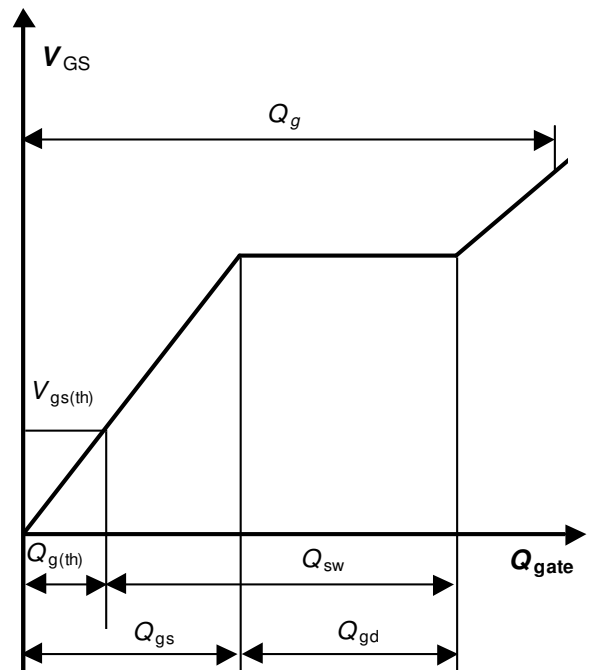


15 Drain-source breakdown voltage

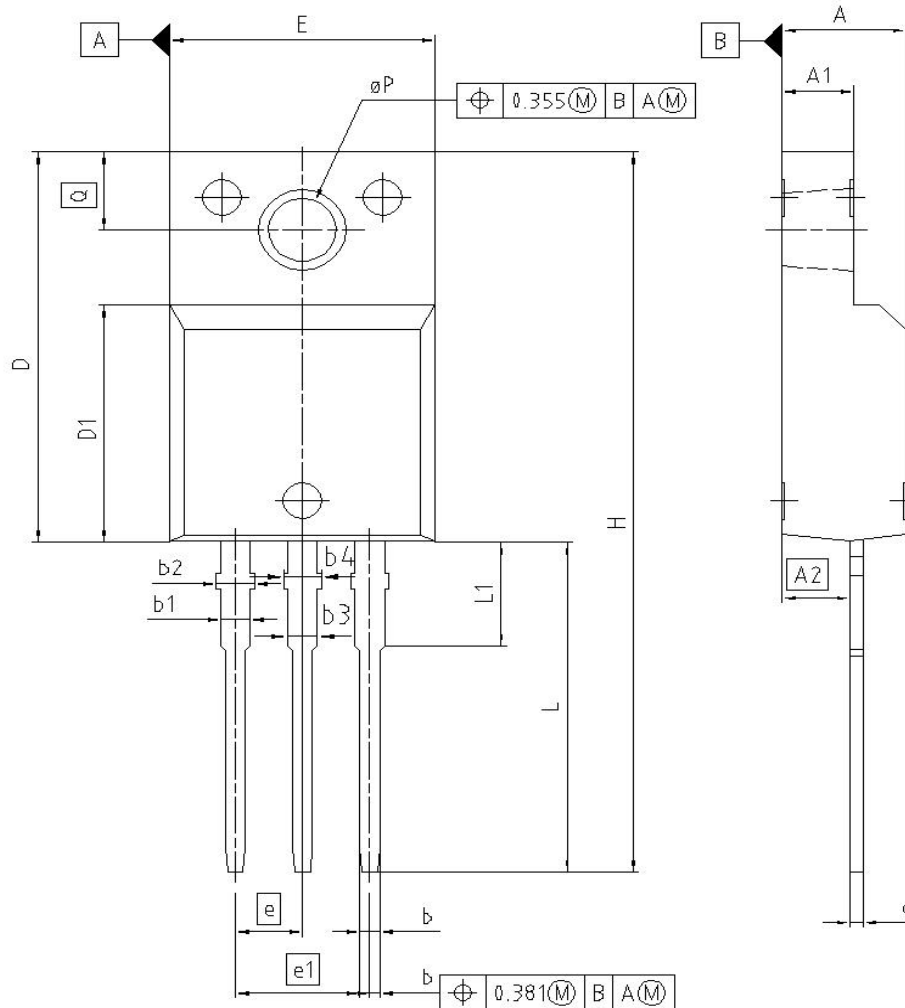
$$V_{BR(DSS)}=f(T_j); I_D=1\ \text{mA}$$



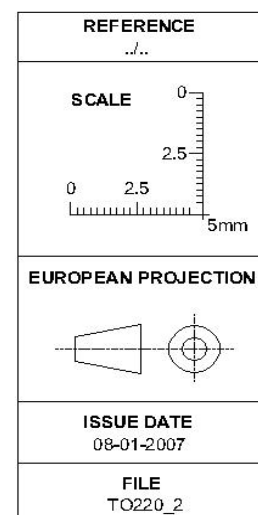
16 Gate charge waveforms



PG-TO220-FP



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.55	4.85	0.179	0.191
A1	2.55	2.85	0.100	0.112
A2	2.42	2.72	0.095	0.107
b	0.65	0.85	0.026	0.033
b1	0.95	1.33	0.037	0.052
b2	0.95	1.51	0.037	0.059
b3	0.65	1.33	0.026	0.052
b4	0.65	1.51	0.026	0.059
c	0.40	0.63	0.016	0.025
D	15.85	16.15	0.624	0.636
D1	9.53	9.83	0.375	0.387
E	10.35	10.65	0.407	0.419
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H	29.45	29.75	1.159	1.171
L	13.45	13.75	0.530	0.541
L1	3.15	3.45	0.124	0.136
ØP	2.95	3.20	0.116	0.126
Q	3.15	3.50	0.124	0.138



Revision History

IPA086N10N3 G

Revision: 2015-08-27, Rev. 2.4

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.4	2015-08-27	Update features: "Fully isolated package..."

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